



Formation of InGaAs layers onto InP substrates by liquid-phase epitaxy

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Abstract

The results of $\text{In}_{0.53}\text{Ga}_{0.47}\text{As}$ InP epitaxial structure interface investigation are presented. It is shown that the transition from InP to $\text{In}_{0.53}\text{Ga}_{0.47}\text{As}$ layer is associated with an interfacial transitional layer formation with a gradient composition. The dynamics of such layer formation has been followed by infrared spectroscopy.